

Edward Yi Chang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Nitrogen-Passivated (010) In _{0.53} Ga _{0.47} As FinFETs With High Peak <i>g_m</i> and Reduced Leakage Current. IEEE Transactions on Electron Devices, 2022, 69, 495-499.	3.0	7
2	Sub-10 nm Top Width Nanowire InGaAs Gate-All-Around MOSFETs With Improved Subthreshold Characteristics and Device Reliability. IEEE Journal of the Electron Devices Society, 2022, 10, 188-191.	2.1	7
3	Extraction of Bias-dependent Source and Drain Resistances in AlGaIn/GaN MIS-HEMTs Using Pulsed Measurement Method. ECS Journal of Solid State Science and Technology, 2022, 11, 065008.	1.8	0
4	Hf-Based and Zr-Based Charge Trapping Layer Engineering for E-Mode GaN MIS-HEMT Using Ferroelectric Charge Trap Gate Stack. IEEE Journal of the Electron Devices Society, 2022, 10, 525-531.	2.1	4
5	Minimum Power Input Control for Class-E Amplifier Using Depletion-Mode Gallium Nitride High Electron Mobility Transistor. Energies, 2021, 14, 2302.	3.1	11
6	Analysis of Instability Behavior and Mechanism of E-Mode GaN Power HEMT with p-GaN Gate under Off-State Gate Bias Stress. Energies, 2021, 14, 2170.	3.1	3
7	Analysis of High-Frequency Behavior of AlGaIn/GaN HEMTs and MIS-HEMTs under UV Illumination. ECS Journal of Solid State Science and Technology, 2021, 10, 055004.	1.8	1
8	Investigation of Multiple-Mesa-Nanochannel Array GaN-Based MOSHEMTs with Al ₂ O ₃ Gate Dielectric Layer. ECS Journal of Solid State Science and Technology, 2021, 10, 055017.	1.8	3
9	The Evolution of Manufacturing Technology for GaN Electronic Devices. Micromachines, 2021, 12, 737.	2.9	23
10	A New GaN-Based Device, P-Cascode GaN HEMT, and Its Synchronous Buck Converter Circuit Realization. Energies, 2021, 14, 3477.	3.1	4
11	AlGaIn/GaN Enhancement-Mode MOSHEMTs Utilizing Hybrid Gate-Recessed Structure and Ferroelectric Charge Trapping/Storage Stacked LiNbO ₃ /HfO ₂ /Al ₂ O ₃ Structure. IEEE Transactions on Electron Devices, 2021, 68, 3768-3774.	3.0	5
12	E-Mode GaN MIS-HEMT Using Ferroelectric Charge Trap Gate Stack With Low Dynamic On-Resistance and High <i>V_{th}</i> Stability by Field Plate Engineering. IEEE Electron Device Letters, 2021, 42, 1268-1271.	3.9	12
13	Development of GaN HEMTs Fabricated on Silicon, Silicon-on-Insulator, and Engineered Substrates and the Heterogeneous Integration. Micromachines, 2021, 12, 1159.	2.9	34
14	Derivation of the Resonance Mechanism for Wireless Power Transfer Using Class-E Amplifier. Energies, 2021, 14, 632.	3.1	11
15	Control of <i>V_{th}</i> of the enhancement high-frequency AlGaIn/GaN HEMT fabricated by oxygen-based digital etching. Applied Physics Express, 2021, 14, 126501.	2.4	2
16	Low resistive InGaN film grown by metalorganic chemical vapor deposition. Vacuum, 2020, 171, 108974.	3.5	7
17	Reliability Characterization of Gallium Nitride MIS-HEMT Based Cascode Devices for Power Electronic Applications. Energies, 2020, 13, 2628.	3.1	14
18	Enhancement of electron transport properties of InAlGaIn/AlN/GaN HEMTs on silicon substrate with GaN insertion layer. Applied Physics Express, 2020, 13, 065501.	2.4	2

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19	High performance UV photodetector based on MoS ₂ layers grown by pulsed laser deposition technique. <i>Journal of Alloys and Compounds</i> , 2020, 835, 155222.	5.5	34
20	Communication—Potential of the ĩ€-Gate InAs HEMTs for High-Speed and Low-Power Logic Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, P319-P321.	1.8	2
21	The effect of a Sb and Ga intermediate layer on the interfacial layer properties of epitaxial GaSb on GaAs grown by metalorganic chemical vapor deposition. <i>Thin Solid Films</i> , 2019, 669, 430-435.	1.8	2
22	Entirely relaxed lattice-mismatched GaSb/GaAs/Si(001) heterostructure grown via metalorganic chemical vapor deposition. <i>Applied Physics Express</i> , 2018, 11, 051202.	2.4	2
23	Comprehensive dynamic on-resistance assessments in GaN-on-Si MIS-HEMTs for power switching applications. <i>Semiconductor Science and Technology</i> , 2018, 33, 055012.	2.0	11
24	In_{0.53}Ga_{0.47}As FinFET and GAA-FET With Remote-Plasma Treatment. <i>IEEE Electron Device Letters</i> , 2018, 39, 339-342.	3.9	19
25	AlGaIn/GaN MIS-HEMTs With High Quality ALD-Al₂O₃ Gate Dielectric Using Water and Remote Oxygen Plasma As Oxidants. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 110-115.	2.1	14
26	High-Performance Normally-OFF GaN MIS-HEMTs Using Hybrid Ferroelectric Charge Trap Gate Stack (FEG-HEMT) for Power Device Applications. <i>IEEE Electron Device Letters</i> , 2018, 39, 991-994.	3.9	35
27	Nonlinear dependence of X-ray diffraction peak broadening in In _x Ga _{1-x} Sb epitaxial layers on GaAs substrates. <i>Applied Physics Express</i> , 2018, 11, 045503.	2.4	3
28	Electrical Properties of Compound 2D Semiconductor Mo_{1-x}Nb_xS₂. , 2018, , .		1
29	High-Performance LPCVD-SiN_x/InAlGaIn/GaN MIS-HEMTs With 850-V 0.98- $\text{ext}\{m\}\{\Omega\}$ cm^2 for Power Device Applications. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 1136-1141.	2.1	18
30	Normally-OFF GaN MIS-HEMT With F⁺ Doped Gate Insulator Using Standard Ion Implantation. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 893-899.	2.1	29
31	A versatile low-resistance ohmic contact process with ohmic recess and low-temperature annealing for GaN HEMTs. <i>Semiconductor Science and Technology</i> , 2018, 33, 095019.	2.0	16
32	InGaAs QW-MOSFET Performance Improvement Using a PEALD-AlN Passivation Layer and an ĩ€-In-Situ NH₃ Post Remote-Plasma Treatment. <i>IEEE Electron Device Letters</i> , 2017, 38, 310-313.	3.9	4
33	Effective Passivation With High-Density Positive Fixed Charges for GaN MIS-HEMTs. <i>IEEE Journal of the Electron Devices Society</i> , 2017, 5, 170-174.	2.1	14
34	Materials growth and band offset determination of Al ₂ O ₃ /In _{0.15} Ga _{0.85} Sb/GaSb/GaAs heterostructure grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	6
35	High-Performance GaN MOSHEMTs Fabricated With ALD Al₂O₃ Dielectric and NBE Gate Recess Technology for High Frequency Power Applications. <i>IEEE Electron Device Letters</i> , 2017, 38, 771-774.	3.9	21
36	Demonstrating antiphase domain boundary-free GaAs buffer layer on zero off-cut Si (0°) substrate for interfacial misfit dislocation GaSb film by metalorganic chemical vapor deposition. <i>Materials Research Express</i> , 2017, 4, 085901.	1.6	4

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37	Study of the interface stability of the metal (Mo, Ni, Pd)/HfO ₂ /AlN/InGaAs MOS devices. AIP Advances, 2017, 7, 085208.	1.3	3
38	Growth of high-quality In _{0.28} Ga _{0.72} Sb/AlSb/GaSb/GaAs heterostructure by metalorganic chemical vapor deposition for single-channel Sb-based complementary metal-oxide-semiconductor applications. Applied Physics Express, 2017, 10, 075505.	2.4	5
39	Improved Linearity in AlGaN/GaN HEMTs for Millimeter-Wave Applications by Using Dual-Gate Fabrication. ECS Journal of Solid State Science and Technology, 2017, 6, S3106-S3109.	1.8	9
40	Evaluation and Reliability Assessment of GaN-on-Si MIS-HEMT for Power Switching Applications. Energies, 2017, 10, 233.	3.1	19
41	Evaluation of AlGaN/GaN metal-oxide-semiconductor high-electron mobility transistors with plasma-enhanced atomic layer deposition HfO ₂ /AlN gate dielectric for RF power applications. Japanese Journal of Applied Physics, 2017, 56, 094101.	1.5	0
42	Impact of interfacial misfit dislocation growth mode on highly lattice-mismatched In _x Ga _{1-x} Sb epilayer grown on GaAs substrate by metalorganic chemical vapor deposition. Applied Physics Letters, 2016, 109, .	3.3	14
43	The effect of surface passivation on the electrical performance of Al-GaN/GaN HEMTs with slant field plates. , 2016, , .		0
44	Enhancement-mode AlGaN/GaN MIS-HEMTs with low threshold voltage hysteresis using damage-free neutral beam etched gate recess. , 2016, , .		1
45	Effective surface treatment for GaN metal-insulator-semiconductor high-electron-mobility transistors using HF plus N ₂ plasma prior to SiN passivation. Japanese Journal of Applied Physics, 2016, 55, 01AD06.	1.5	6
46	Study on the electrical characteristics of in situ PEALD-passivated HfO ₂ /In _{0.53} Ga _{0.47} As MOSCAP and MOSFET structures. , 2016, , .		0
47	Performance Enhancement of Flip-Chip Packaged AlGaN/GaN HEMTs by Strain Engineering Design. IEEE Transactions on Electron Devices, 2016, 63, 3876-3881.	3.0	2
48	Electrical Analysis and PBTI Reliability of In _{0.53} Ga _{0.47} As MOSFETs With AlN Passivation Layer and NH ₃ Postremote Plasma Treatment. IEEE Transactions on Electron Devices, 2016, 63, 3466-3472.	3.0	8
49	Investigation of Multilayer TiNi Alloys as the Gate Metal for nMOS In _{0.53} Ga _{0.47} As. IEEE Transactions on Electron Devices, 2016, 63, 4714-4719.	3.0	4
50	Methods for Extracting Flat Band Voltage in the InGaAs High Mobility Materials. IEEE Electron Device Letters, 2016, 37, 1100-1103.	3.9	7
51	Improved linearity and reliability in GaN metal-oxide-semiconductor high-electron-mobility transistors using nanolaminate La ₂ O ₃ /SiO ₂ gate dielectric. Japanese Journal of Applied Physics, 2016, 55, 04EG04.	1.5	14
52	A 60-nm-thick enhancement mode In _{0.65} Ga _{0.35} As/InAs/In _{0.65} Ga _{0.35} As high-electron-mobility transistor fabricated using Au/Pt/Ti non-annealed ohmic technology for low-power logic applications. Applied Physics Express, 2016, 9, 026502.	2.4	3
53	Effects of In-Situ Plasma-Enhanced Atomic Layer Deposition Treatment on the Performance of HfO ₂ /In _{0.53} Ga _{0.47} As Metal-Oxide-Semiconductor Field-Effect Transistors. IEEE Electron Device Letters, 2016, , 1-1.	3.9	21
54	Optimal design of the multiple-apertures-GaN-based vertical HEMTs with SiO_2 current blocking layer. Journal of Computational Electronics, 2016, 15, 154-162.	2.5	12

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55	Effect of high voltage stress on the DC performance of the Al ₂ O ₃ /AlN GaN metal-insulator-semiconductor high-electron mobility transistor for power applications. Applied Physics Express, 2015, 8, 104102.	2.4	6
56	Impact of AlN Interfacial Dipole on Effective Work Function of Ni and Band Alignment of Ni/HfO ₂ /In _{0.53} Ga _{0.47} As Gate-Stack. IEEE Transactions on Electron Devices, 2015, 62, 3987-3991.	3.0	13
57	Potential of Enhancement Mode In _{0.65} Ga _{0.35} As/InAs/In _{0.65} Ga _{0.35} As HEMTs for Using in High-Speed and Low-Power Logic Applications. ECS Journal of Solid State Science and Technology, 2015, 4, N157-N159.	1.8	9
58	Layered MoS ₂ grown on c-sapphire by pulsed laser deposition. Physica Status Solidi - Rapid Research Letters, 2015, 9, 187-191.	2.4	130
59	Plasma Enhanced Atomic Layer Deposition Passivated HfO ₂ /AlN/In _{0.53} Ga _{0.47} As MOSCAPs With Sub-Nanometer Equivalent Oxide Thickness and Low Interface Trap Density. IEEE Electron Device Letters, 2015, 36, 1277-1280.	3.9	30
60	An Au-free GaN high electron mobility transistor with Ti/Al/W Ohmic metal structure. , 2015, , .		1
61	A novel AlGaIn/GaN multiple aperture vertical high electron mobility transistor with silicon oxide current blocking layer. Vacuum, 2015, 118, 59-63.	3.5	20
62	Electrical Characteristics of n, p-In _{0.53} Ga _{0.47} As MOSCAPs With In Situ PEALD-AlN Interfacial Passivation Layer. IEEE Transactions on Electron Devices, 2014, 61, 2774-2778.	3.0	39
63	Effect of annealing processes on the electrical properties of the atomic layer deposition Al ₂ O ₃ /In _{0.53} Ga _{0.47} As metal oxide semiconductor capacitors. Japanese Journal of Applied Physics, 2014, 53, 04EF04.	1.5	10
64	High quality Ge epitaxial films grown on In _{0.51} Ga _{0.49} P/GaAs and GaAs substrates by ultra high vacuum chemical deposition. , 2014, , .		0
65	Effects of initial GaN growth mode on the material and electrical properties of AlGaIn/GaN high-electron-mobility transistors. Applied Physics Express, 2014, 7, 095502.	2.4	6
66	Gate Recessed Quasi-Normally OFF Al ₂ O ₃ /AlGaIn/GaN MIS-HEMT With Low Threshold Voltage Hysteresis Using PEALD AlN Interfacial Passivation Layer. IEEE Electron Device Letters, 2014, 35, 732-734.	3.9	91
67	GaN MIS-HEMTs With Nitrogen Passivation for Power Device Applications. IEEE Electron Device Letters, 2014, 35, 1001-1003.	3.9	70
68	Simulation study on electrical characteristic of AlGaIn/GaN high electron mobility transistors with AlN spacer layer. Japanese Journal of Applied Physics, 2014, 53, 04EF08.	1.5	34
69	The effect of CdS QDs structure on the InGaP/GaAs/Ge triple junction solar cell efficiency. Electronic Materials Letters, 2014, 10, 457-460.	2.2	5
70	Performance Enhancement of Flip-Chip Packaged AlGaIn/GaN HEMTs Using Active-Region Bumps-Induced Piezoelectric Effect. IEEE Electron Device Letters, 2014, 35, 735-737.	3.9	6
71	Coherent phonon manipulation in coupled mechanical resonators. Nature Physics, 2013, 9, 480-484.	16.7	274
72	Demonstrating 1-nm-oxide-equivalent-thickness HfO ₂ /InSb structure with unpinning Fermi level and low gate leakage current density. Applied Physics Letters, 2013, 103, 142903.	3.3	8

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73	Ge epitaxial films on GaAs (100), (110), and (111) substrates for applications of CMOS heterostructural integrations. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, .	1.2	4
74	Electrical Characterization and Materials Stability Analysis of $\text{La}_2\text{O}_3/\text{HfO}_2$ Composite Oxides on n- $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOS Capacitors With Different Annealing Temperatures. IEEE Electron Device Letters, 2013, 34, 1229-1231.	3.9	15
75	Studying of InSb MOS capacitors for post CMOS application. , 2013, , .		0
76	Room temperature self-organized gold nanoparticles materials for embedded electronic devices. Journal of Materials Science: Materials in Electronics, 2013, 24, 376-381.	2.2	2
77	Investigation of Characteristics of $\text{Al}_2\text{O}_3/\text{In}_x\text{Ga}_{1-x}\text{As}$ ($x=0.53, 0.7, \text{ and } 1$) Metalâ€“Oxideâ€“Semiconductor Structures. Journal of Electronic Materials, 2013, 42, 2439-2444.	2.2	2
78	Performance Evaluation of InGaSb/AlSb P-Channel High-Hole-Mobility Transistor Fabricated Using BCl ₃ Dry Etching. Japanese Journal of Applied Physics, 2013, 52, 020203.	1.5	2
79	Electrical Characteristics of $\text{Al}_2\text{O}_3/\text{InSb}$ MOSCAPs and the Effect of Postdeposition Annealing Temperatures. IEEE Transactions on Electron Devices, 2013, 60, 1555-1560.	3.0	13
80	Band Alignment Parameters of $\text{Al}_2\text{O}_3/\text{InSb}$ Metalâ€“Oxideâ€“Semiconductor Structure and Their Modification with Oxide Deposition Temperatures. Applied Physics Express, 2013, 6, 061202.	2.4	16
81	Influence of post deposition annealing temperatures on electrical properties of $\text{Al}_2\text{O}_3/\text{InSb}$ MOSCAPs. , 2012, , .		1
82	Impact of bonding temperature on the performance of $\text{In}_{0.6}\text{Ga}_{0.4}\text{As}$ Metamorphic High Electron Mobility Transistor (mHEMT) device packaged using Flip-Chip-on-Board (FCOB) technology. , 2012, , .		0
83	Fabrication of AlGaIn/GaN high electron mobility transistors (HEMTs) on silicon substrate with slant field plates using deep-UV lithography featuring 5W/mm power density at X-band. , 2012, , .		4
84	Effect of Postdeposition Annealing Temperatures on Electrical Characteristics of Molecular-Beam-Deposited HfO_2 on n-InAs/InGaAs Metalâ€“Oxideâ€“Semiconductor Capacitors. Applied Physics Express, 2012, 5, 021104.	2.4	17
85	Design, Fabrication, and Reliability of Low-Cost Flip-Chip-On-Board Package for Commercial Applications up to 50 GHz. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 402-409.	2.5	8
86	Bias-Dependent Radio Frequency Performance for 40 nm InAs High-Electron-Mobility Transistor with a Cutoff Frequency Higher than 600 GHz. Japanese Journal of Applied Physics, 2012, 51, 110203.	1.5	5
87	Effect of Nitridation on the Regrowth Interface of AlGaIn/GaN Structures Grown by Molecular Beam Epitaxy on GaN Templates. Journal of Electronic Materials, 2012, 41, 2139-2144.	2.2	6
88	Câ€“V characteristics of epitaxial germanium metalâ€“oxideâ€“semiconductor capacitor on GaAs substrate with ALD Al_2O_3 dielectric. Microelectronic Engineering, 2012, 97, 16-19.	2.4	4
89	3D finite element simulation of morphological effect on reflectance of Si_3N_4 sub-wavelength structures for silicon solar cells. , 2011, , .		0
90	High quality Ge thin film grown by ultrahigh vacuum chemical vapor deposition on GaAs substrate. Applied Physics Letters, 2011, 98, .	3.3	32

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91	Experimental and Modeling on Atomic Layer Deposition Al ₂ O ₃ /n-InAs Metal-Oxide-Semiconductor Capacitors with Various Surface Treatments. ECS Transactions, 2011, 34, 1041-1046.	0.5	1
92	Dislocation reduction in GaN film using Ga-lean GaN buffer layer and migration enhanced epitaxy. Thin Solid Films, 2011, 519, 6208-6213.	1.8	14
93	Shape Effect of Silicon Nitride Subwavelength Structure on Reflectance for Silicon Solar Cells. IEEE Transactions on Electron Devices, 2010, 57, 2427-2433.	3.0	30
94	Novel Metamorphic HEMTs With Highly Doped InGaAs Source/Drain Regions for High Frequency Applications. IEEE Transactions on Electron Devices, 2010, 57, 2594-2598.	3.0	13
95	Design of Flip-Chip Interconnect Using Epoxy-Based Underfill Up to V-Band Frequencies With Excellent Reliability. IEEE Transactions on Microwave Theory and Techniques, 2010, 58, 2244-2250.	4.6	8
96	Finite element analysis of antireflective silicon nitride sub-wavelength structures for solar cell applications. Thin Solid Films, 2010, 518, 7204-7208.	1.8	6
97	Study of the inversion behaviors of Al ₂ O ₃ /In _x Ga _{1-x} As metal-oxide-semiconductor capacitors with different In contents. Solid-State Electronics, 2010, 54, 37-41.	1.4	18
98	An Al ₂ O ₃ /AlGaAs/InGaAs Metal-Oxide-Semiconductor PHEMT SPDT Switch with Low Control Currents for Wireless Communication Applications. Electrochemical and Solid-State Letters, 2010, 13, H219.	2.2	0
99	Electrical Characterization and Transmission Electron Microscopy Assessment of Isolation of AlGaN/GaN High Electron Mobility Transistors with Oxygen Ion Implantation. Japanese Journal of Applied Physics, 2010, 49, 021001.	1.5	2
100	The Roles of Threading Dislocations on Electrical Properties of AlGaN/GaN Heterostructure Grown by MBE. Journal of the Electrochemical Society, 2010, 157, H746.	2.9	62
101	Effects of Wet Chemical and Trimethyl Aluminum Treatments on the Interface Properties in Atomic Layer Deposition of Al ₂ O ₃ on InAs. Japanese Journal of Applied Physics, 2010, 49, 111201.	1.5	29
102	Design and Fabrication of 0/1-Level RF-Via Interconnect for RF-MEMS Packaging Applications. IEEE Transactions on Advanced Packaging, 2010, 33, 30-36.	1.6	7
103	InAs-Channel Metal-Oxide-Semiconductor HEMTs with Atomic-Layer-Deposited Al ₂ O ₃ Gate Dielectric. Electrochemical and Solid-State Letters, 2009, 12, H456.	2.2	1
104	InAs-Channel High-Electron-Mobility Transistors for Ultralow-Power Low Noise Amplifier Applications. Japanese Journal of Applied Physics, 2009, 48, 04C094.	1.5	1
105	Numerical calculation of the reflectance of sub-wavelength structures on silicon nitride for solar cell application. Computer Physics Communications, 2009, 180, 1721-1729.	7.5	16
106	The effect of AlN buffer growth parameters on the defect structure of GaN grown on sapphire by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1487-1492.	1.5	15
107	Changes of Electrical Characteristics for AlGaN/GaN HEMTs Under Uniaxial Tensile Strain. IEEE Electron Device Letters, 2009, 30, 213-215.	3.9	43
108	A 40-nm-Gate InAs/In _{0.7} Ga _{0.3} As Composite-Channel HEMT with 2200 mS/mm and 500-GHz f _T . , , 2009, , .		0

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109	RF and Logic Performance Improvement of $\text{In}_{0.7}\text{Ga}_{0.3}\text{As}/\text{InAs}/\text{In}_{0.7}\text{Ga}_{0.3}\text{As}$ Composite-Channel HEMT Using Gate-Sinking Technology. IEEE Electron Device Letters, 2008, 29, 290-293.	3.9	26
110	Dependence of GaN Defect Structure on the Growth Temperature of the AlN Buffer Layer. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	0
111	On the noise performance of 80nm $\text{InAs}/\text{In}_{0.7}\text{Ga}_{0.3}\text{As}$ HEMTs using gate sinking technology. , 2008, , .		0
112	InAs Channel-Based Quantum Well Transistors for High-Speed and Low-Voltage Digital Applications. Electrochemical and Solid-State Letters, 2008, 11, H193.	2.2	8
113	An AlGaAs/InGaAs HEMT Grown on Si Substrate with Ge/CexSi1-x Metamorphic Buffer Layers. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	0
114	Hybridization sensing by electrical enhancement with nanoparticles in nanogap. Journal of Vacuum Science & Technology B, 2008, 26, 2572-2577.	1.3	5
115	AlGaAs/InGaAs High Electron Mobility Transistor Grown on Si Substrate with Ge/CexSi1-x Metamorphic Buffer Layers. Japanese Journal of Applied Physics, 2008, 47, 7069-7072.	1.5	4
116	High-speed GaAs metal gate semiconductor field effect transistor structure grown on a composite $\text{Ge}\cdot\text{CexSi1-x}\cdot\text{Si}$ substrate. Journal of Applied Physics, 2007, 101, 084501.	2.5	24
117	Oxygen Ion Implantation Isolation Planar Process for AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2007, 28, 476-478.	3.9	44
118	Investigation of Impact Ionization in InAs-Channel HEMT for High-Speed and Low-Power Applications. IEEE Electron Device Letters, 2007, 28, 856-858.	3.9	39
119	Evaluation of RF and Logic Performance for 80 nm InAs/InGaAs Composite Channel HEMTs Using Gate Sinking Technology. , 2007, , .		1
120	60 GHz Broadband MS-to-CPW Hot-Via Flip Chip Interconnects. IEEE Microwave and Wireless Components Letters, 2007, 17, 784-786.	3.2	16
121	A δ -Doped InGaP/InGaAs pHEMT With Different Doping Profiles for Device-Linearity Improvement. IEEE Transactions on Electron Devices, 2007, 54, 1617-1625.	3.0	23
122	Growth of High-Quality Ge Epitaxial Layers on Si (100). Japanese Journal of Applied Physics, 2003, 42, L517-L519.	1.5	32